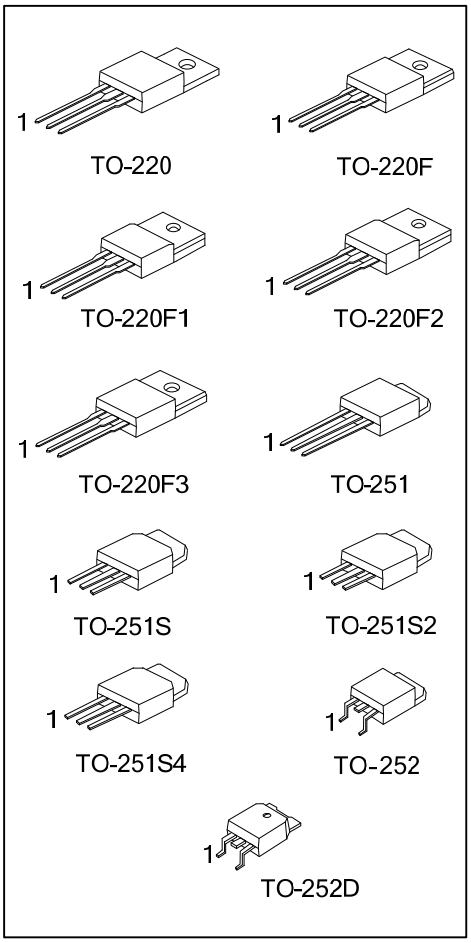
5N65K-MTQ

Power MOSFET

5A, 650V N-CHANNEL POWER MOSFET



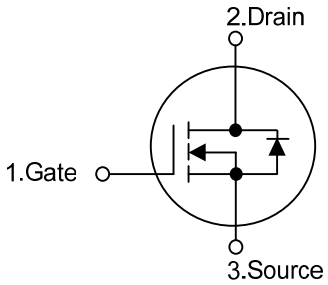
■ DESCRIPTION

The UTC **5N65K-MTQ** is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications at power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

■ FEATURES

* $R_{DS(ON)}$ < 2.2Ω @ V_{GS} = 10 V, I_D = 2.5 A
* Fast Switching Capability
* Improved dv/dt Capability, High Ruggedness

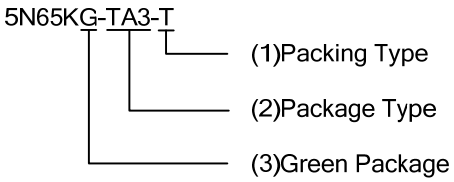
■ SYMBOL



■ ORDERING INFORMATION

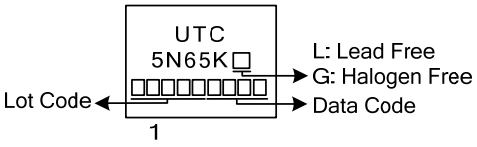
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
5N65KL-TA3-T	5N65KG-TA3-T	TO-220	G	D	S	Tube
5N65KL-TF3-T	5N65KG-TF3-T	TO-220F	G	D	S	Tube
5N65KL-TF1-T	5N65KG-TF1-T	TO-220F1	G	D	S	Tube
5N65KL-TF2-T	5N65KG-TF2-T	TO-220F2	G	D	S	Tube
5N65KL-TF3-T	5N65KG-TF3-T	TO-220F3	G	D	S	Tube
5N65KL-TM3-T	5N65KG-TM3-T	TO-251	G	D	S	Tube
5N65KL-TMS-T	5N65KG-TMS-T	TO-251S	G	D	S	Tube
5N65KL-TMS2-T	5N65KG-TMS2-T	TO-251S2	G	D	S	Tube
5N65KL-TMS4-T	5N65KG-TMS4-T	TO-251S4	G	D	S	Tube
5N65KL-TN3-R	5N65KG-TN3-R	TO-252	G	D	S	Tape Reel
5N65KL-TND-R	5N65KG-TND-R	TO-252D	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source



(1) T: Tube, R: Tape Reel
(2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2, TF3: TO-220F3, TM3: TO-251 TMS: TO-251S, TMS2: TO-251S2, TMS4: TO-251S4, TN3: TO-252, TND: TO-252D
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current		I_D	5	A
Pulsed Drain Current (Note 2)		I_{DM}	20	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	264	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	6.5	V/ns
Power Dissipation	TO-220	P_D	108	W
	TO-220F/TO-220F1 TO-220F3		36	
	TO-220F2		38	
	TO-251/TO-251S TO-251S2/TO-251S4 TO-252/TO-252D		54	
Junction Temperature		T_J	+150	°C
Operation Temperature		T_{OPR}	-55 ~ +150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L=25mH, I_{AS}=4.6A, V_{DD}=50V, R_G=25 Ω, Starting T_J = 25°C
4. I_{SD}≤5A, di/dt≤200A/μs, V_{DD}≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL RESISTANCES CHARACTERISTICS

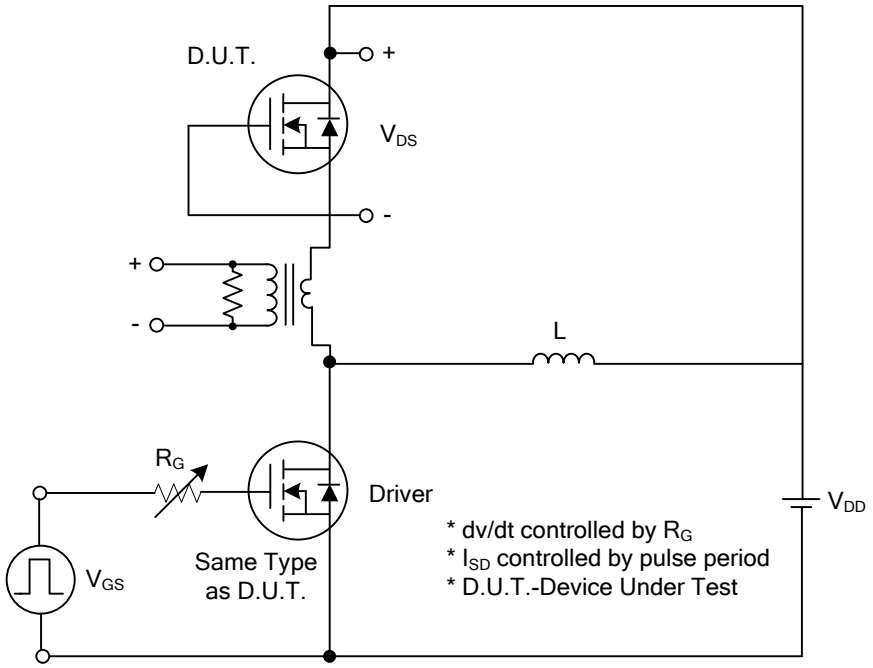
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2 TO-220F3	θ_{JA}	62.5	°C/W
	TO-251/TO-251S TO-251S2/TO-251S4 TO-252/TO-252D		110	°C/W
Junction to Case	TO-220	θ_{JC}	1.15	°C/W
	TO-220F/TO-220F1 TO-220F3		3.47	°C/W
	TO-220F2		3.28	°C/W
	TO-251/TO-251S TO-251S2/TO-251S4 TO-252/TO-252D		2.3	°C/W

■ ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise specified)

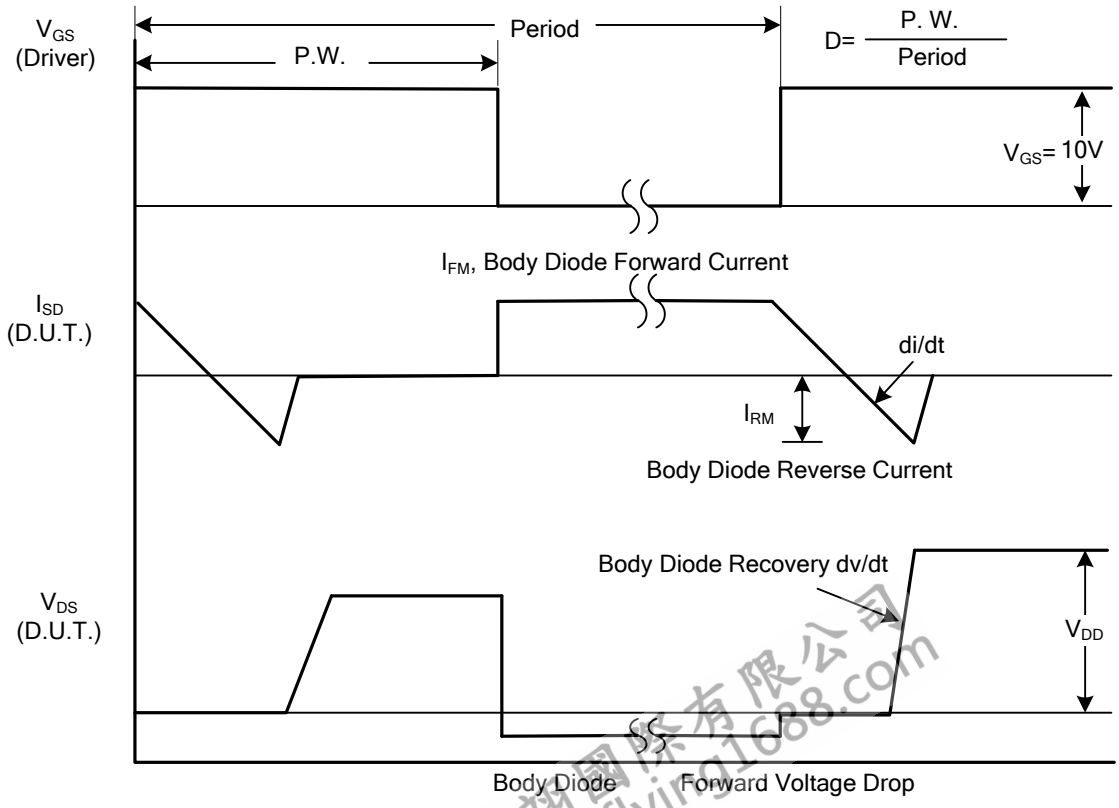
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS} =0V, I_D = 250μA	650			V
Drain-Source Leakage Current		I_{DSS}	V_{DS} =650V, V_{GS} = 0V			1	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS} =30V, V_{DS} = 0V			100	nA
	Reverse		V_{GS} =-30V, V_{DS} = 0V			-100	
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS} =V_{GS}, I_D = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS} =10V, I_D = 2.5A			2.2	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz		636		pF
Output Capacitance		C_{OSS}			69		pF
Reverse Transfer Capacitance		C_{RSS}			4.3		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge		Q_G	V_{DS} = 100 V, I_D = 5.0A, I_D = 1mA, V_{GS} = 10 V (Note 1, 2)		14.5		nC
Gate-Source Charge		Q_{GS}			7.2		nC
Gate-Drain Charge		Q_{GD}			2.5		nC
Turn-On Delay Time		$t_{D(ON)}$	V_{DD} = 30V, I_D = 5.0A, V_{GS}= 10V R_G = 25Ω (Note 1, 2)		46		ns
Turn-On Rise Time		t_R			25		ns
Turn-Off Delay Time		$t_{D(OFF)}$			114		ns
Turn-Off Fall Time		t_F			27		ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
Maximum Continuous Drain-Source Diode Forward Current		I_S				5	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}				20	A
Drain-Source Diode Forward Voltage		V_{SD}	V_{GS} = 0 V, I_S = 5A			1.4	V
Body Diode Reverse Recovery Time		t_{rr}	I_S=5.0A, V_{GS}=0V, dI_F/dt=100A/μs		280		nS
Body Diode Reverse Recovery Charge		Q_{rr}			3.0		μC

Note: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

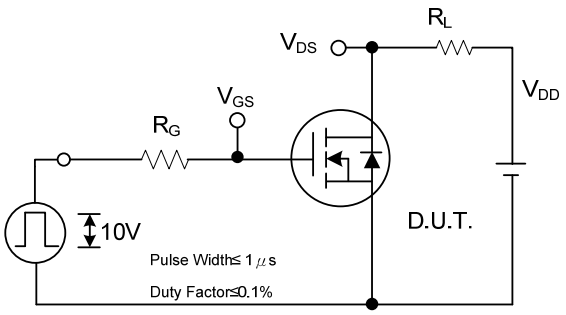


Peak Diode Recovery dv/dt Test Circuit

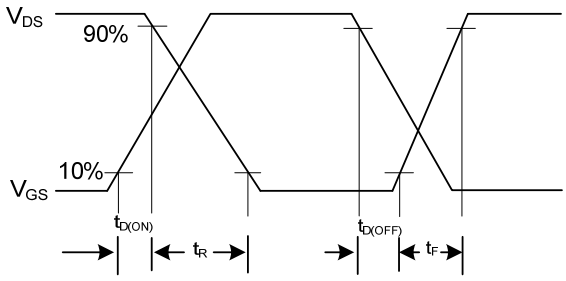


Peak Diode Recovery dv/dt Waveforms

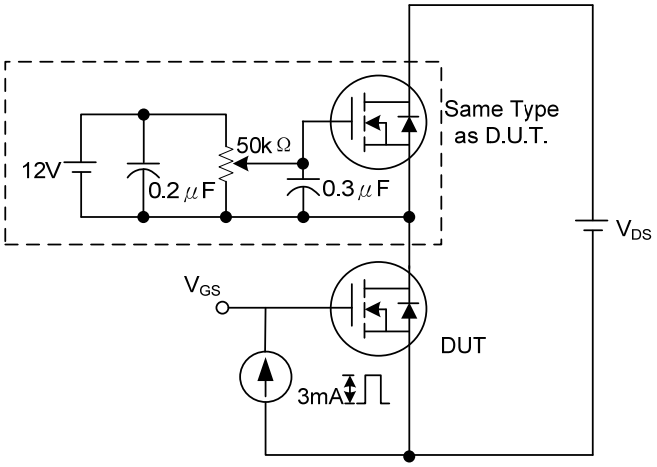
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



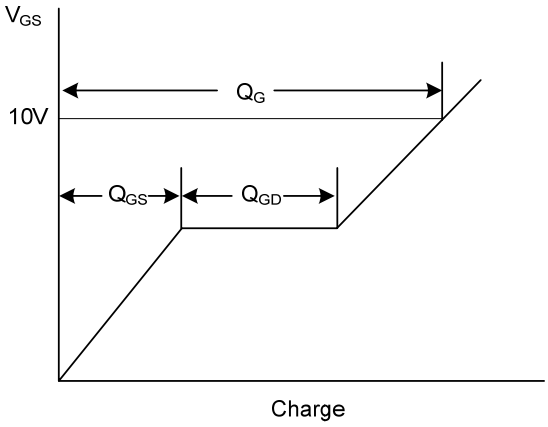
Switching Test Circuit



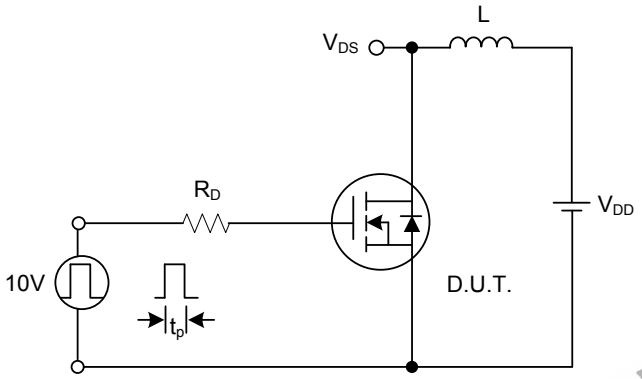
Switching Waveforms



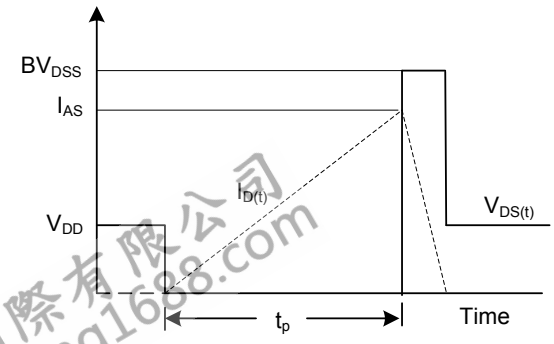
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms